

**1N4448WS** FAST SWITCHING DIODES**FEATURES**

- Fast Switching Speed
- Surface Mount Package Ideally Suited for Automatic Insertion
- For General Purpose Switching Applications
- High Conductance

SOD-323**Maximum Ratings and Electrical Characteristics, Single Diode @T_A=25°C**

Parameter	Symbol	Limits	Unit
Non-Repetitive Peak reverse voltage	V _{RM}	100	V
Peak Repetitive Peak reverse voltage Working Peak DC Blocking Voltage	V _{RRM} V _{RWM} V _R	75	V
RMS Reverse Voltage	V _{R(RMS)}	53	V
Forward Continuous Current	I _{FM}	500	mA
Average Rectified Output Current	I _O	250	mA
Peak forward surge current @=1.0μs @=1.0s	I _{FSM}	4.0 1.5	A
Power Dissipation	P _d	200	mW
Thermal Resistance Junction to Ambient	R _{θJA}	625	°C/W
Storage temperature	T _{STG}	-65~+150	°C

Electrical Ratings @T_A=25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	V _{(BR)R}	75			V	I _R =10μA
Forward voltage	V _{F1}	0.62		0.72	V	I _F =5mA
	V _{F2}			0.855	V	I _F =10mA
	V _{F3}			1.0	V	I _F =100mA
	V _{F4}			1.25	V	I _F =150mA
Reverse current	I _{R1}			2.5	μA	V _R =75V
	I _{R2}			25	nA	V _R =20V
Capacitance between terminals	C _T			4	pF	V _R =0V, f=1MHz
Reverse Recovery Time	t _{rr}			4	ns	I _F =I _R =10mA I _{rr} =0.1I _R , R _L =100Ω

Typical Characteristics 1N4448WS

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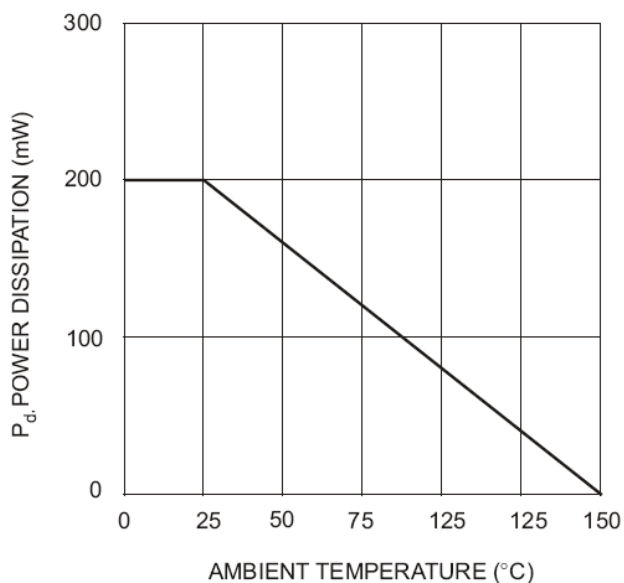


Fig. 1 Forward Current Derating Curve

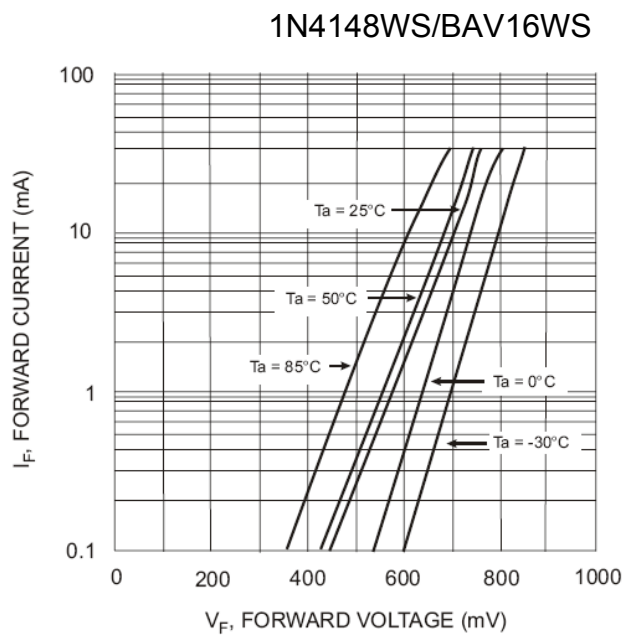


Fig. 2 Typical Forward Characteristics

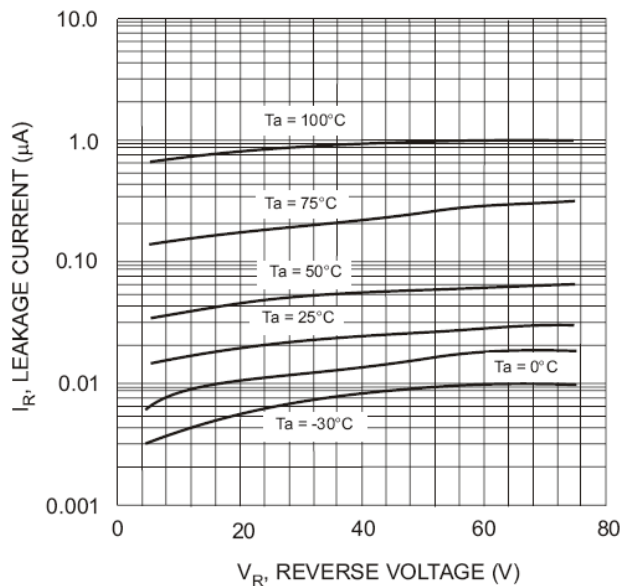


Fig. 3 Typical Reverse Characteristics

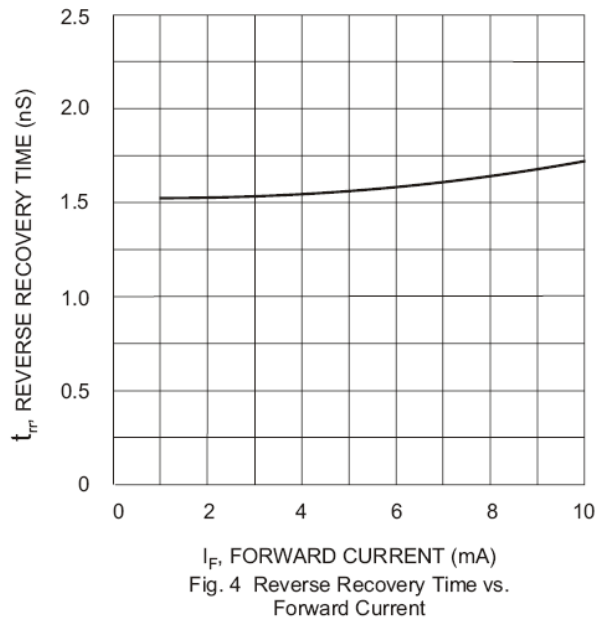


Fig. 4 Reverse Recovery Time vs. Forward Current

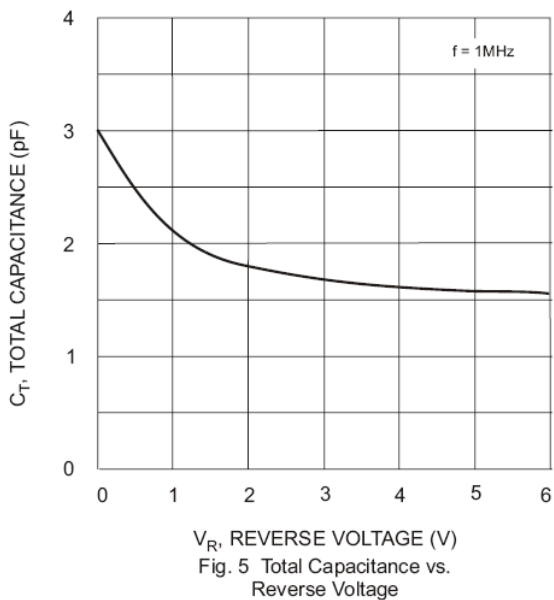


Fig. 5 Total Capacitance vs. Reverse Voltage